

# MC simulation for GaAs sensor and Tungsten for e<sup>-</sup> at 4 GeV

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22<sup>nd</sup> FCAL Collaboration Workshop | 2013 | IFJ PAN | Poland





# Simulation set-up

- ✓ Longitudinal distribution of the EM shower
- ✓ Transversal distribution of the EM shower
- ✓ Conclusions



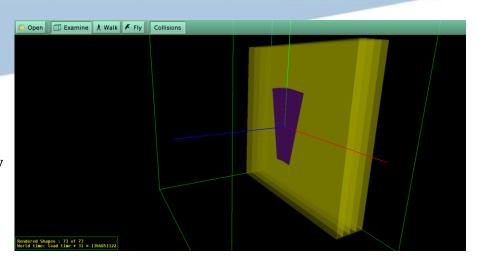
## Monte Carlo simulation with Geant4

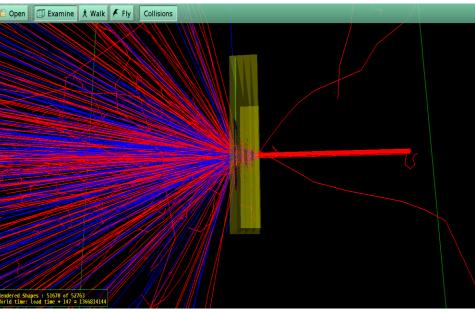
set-up geometry

- 300 µm GaAs sensor
- 2 plate  $Ni = 100 \ \mu m$
- tungsten plate thickness,  $t = 2X_0$ , for tungsten  $X_0 = 0,3504$  cm

#### Particle Gun definition:

- incident particles: e-
- beam energy: 4 GeV
- Gauss distribution of beam with  $\sigma = 3 mm$



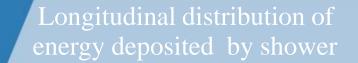


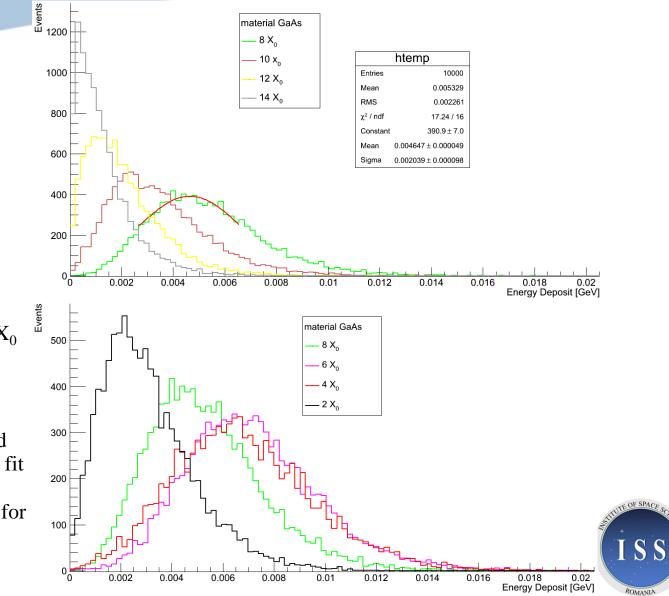
Tracking example for 8  $X_0$  tungsten



#### **Tracking Cuts**

- applied only for GaAs sensor
- we used *fStopAndKill* method to stop any gamma particles



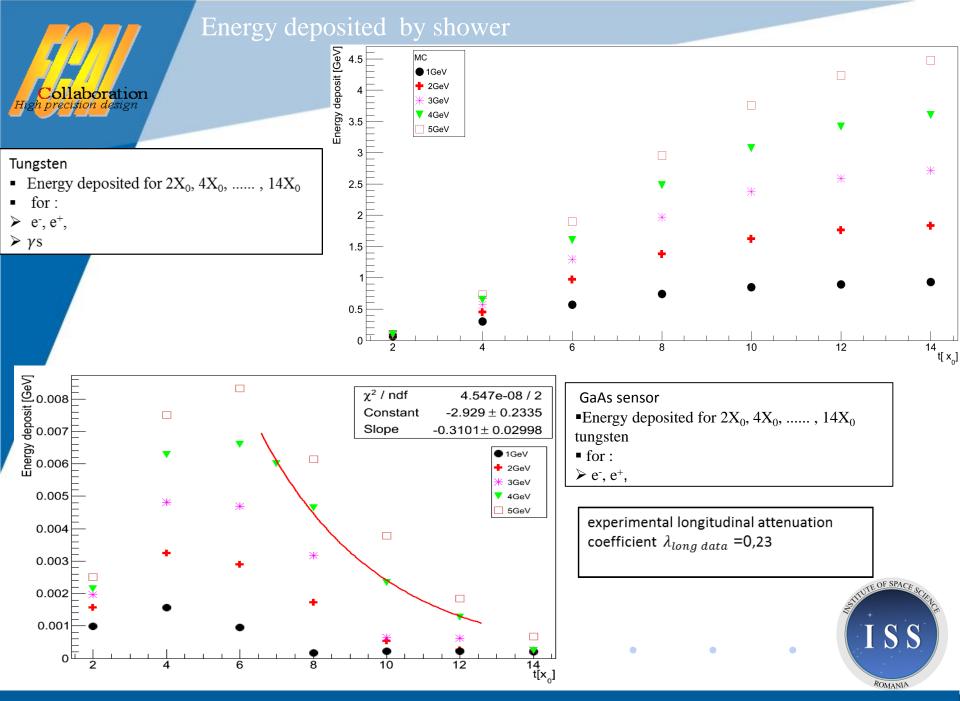


 in GaAs
 For 2X<sub>0</sub>, 4X<sub>0</sub>, ....., 14X<sub>0</sub> tungsten

aboration

- MPV of energy deposited was determened by Gauss fit
- Geant4 dosen't correctly determine the energy loss for thin thickness materials

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## Radial shower development

#### Beam

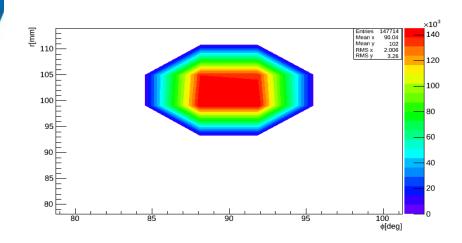
projection on sensor: square L=7mm
intensity: Gaussian, σ = 3.5

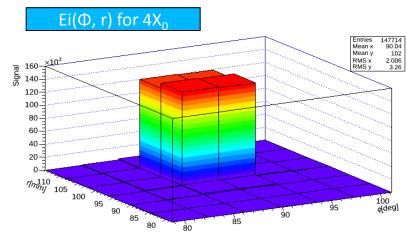
### ✓ No noise included

### ✓ For GaAs

- 1. e⁺, e⁻, gamma
- 2. Only  $e^+$  and  $e^-$  were taking into account

### $\checkmark \mathsf{Ei}(r, \Phi)$ - Distribution of Energy deposition on i-th pads





18

17

16

15

φ=78.75<sup>0</sup>

20

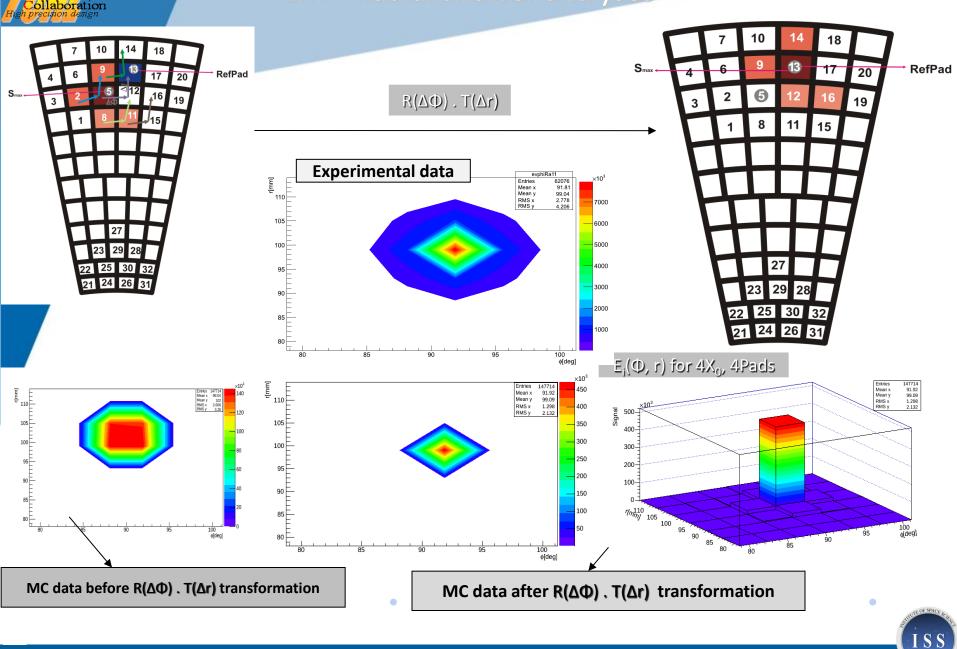
19

3

30

24 26 31

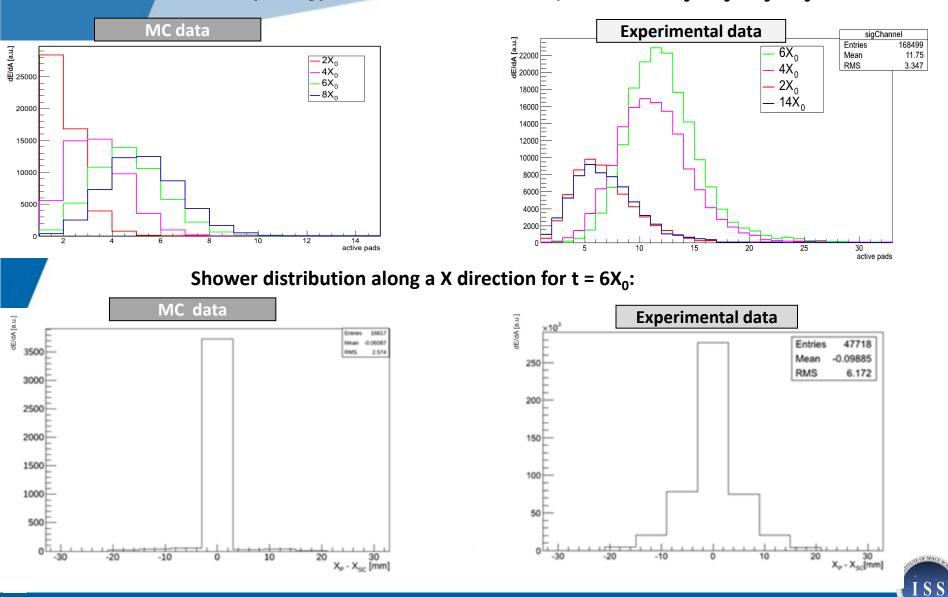
## EM – Radial shower analyses



## EM – Radial shower analyses

boration

Density energy distribution of the active pads for  $t = 2X_0$ ,  $4X_0$ ,  $6X_0$ ,  $8X_0$ 



## Conclusion

Test-beam 2011 set-up geometry was implemented in Geant4;

- It were studied the longitudinal and transversal shower evolution for 4 GeV incident electrons
- ✓ It was developed the same analysis method as with experimental data
- ✓ The future plan:
  - Implemented more realistic behaiviour of GaAs sensor
  - Implemented the fluctuation of the energy loss for this GaAs (300 $\mu m$ )





# THANK YOU FOR ATTENTION!



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